2SC3506

Silicon NPN triple diffusion planar type

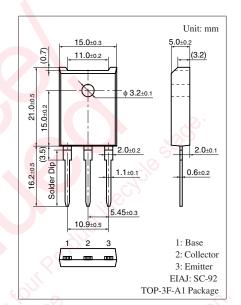
For high-speed switching

■ Features

- High-speed switching
- High collector-base voltage (Emitter open) V_{CBO}
- Satisfactory linearity of forward current transfer ratio h_{FE}
- Full-pack package which can be installed to the heat sink with one screw

■ Absolute Maximum Ratings $T_C = 25^{\circ}C$

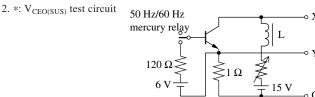
Parameter	Symbol	Rating	Unit	
Collector-base voltage (Emitter open)	V_{CBO}	1 000	V	
Collector-emitter voltage (E-B short)	V _{CES}	1 000	V	
Collector-emitter voltage (Base open)	V _{CEO}	800	V	
Emitter-base voltage (Collector open)	V_{EBO}	7	V	
Collector current	I_{C}	3	A	
Base current	I_B	2	A	
Peak collector current	I_{CP}	6	A	
Collector power dissipation	P _C	70	W	
$T_a = 25^{\circ}C$		3.0	160,	
Junction temperature	T _j	150	°C (
Storage temperature	T_{stg}	-55 to +150	°C	



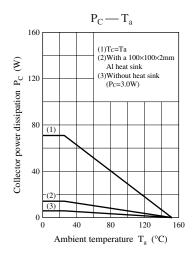
■ Electrical Characteristics $T_C = 25^{\circ}C \pm 3^{\circ}C$

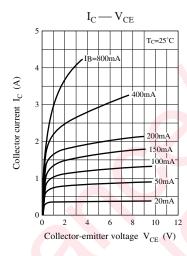
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-emitter sustaining voltage *	V _{CEO(SUS)}	$I_C = 0.5 \text{ A}, L = 50 \text{ mH}$	800			V
Collector-base cutoff current (Emitter open)	I_{CBO}	$V_{CB} = 1000 \text{ V}, I_E = 0$	1.1		50	μΑ
Emitter-base cutoff current (Collector open)	I _{EBO}	$V_{EB} = 7 \text{ V}, I_{C} = 0$			50	μΑ
Forward current transfer ratio	h _{FE}	$V_{CE} = 5 \text{ V}, I_{C} = 2 \text{ A}$	6			_
Collector-emitter saturation voltage	V _{CE(sat)}	$I_C = 2 A, I_B = 0.4 A$			1.5	V
Base-emitter saturation voltage	V _{BE(sat)}	$I_C = 2 \text{ A}, I_B = 0.4 \text{ A}$			1.5	V
Transition frequency	f_T	$V_{CE} = 5 \text{ V}, I_{C} = 0.2 \text{ A}, f = 1 \text{ MHz}$		4		MHz
Turn-on time	t _{on}	$I_C = 2 A$			1	μs
Storage time	t _{stg}	$I_{B1} = 0.4 \text{ A}, I_{B2} = -0.8 \text{ A}$			2.5	μs
Fall time	t _f	$V_{CC} = 250 \text{ V}$			0.5	μs

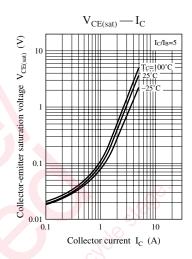
 $Note) \ 1. \ Measuring \ methods \ are \ based \ on \ JAPANESE \ INDUSTRIAL \ STANDARD \ JIS \ C \ 7030 \ measuring \ methods \ for \ transistors.$

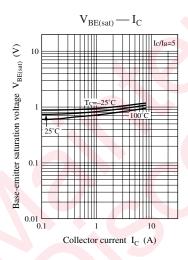


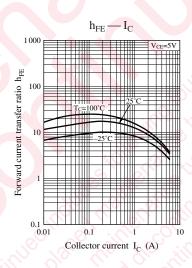
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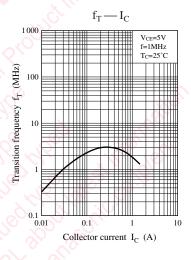


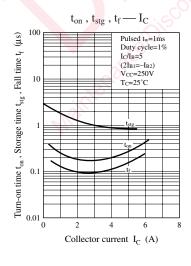


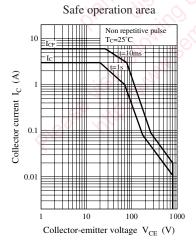




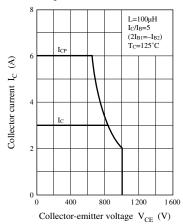




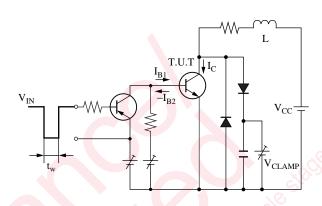


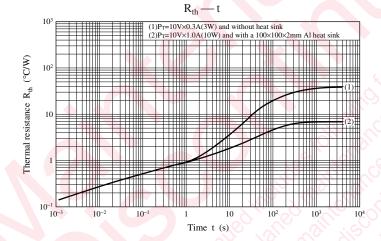


Safe operation area (Reverse bias)



Safe operation area (Reverse bias) measurement circuit





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